

POINT DEFECTS AND MECHANISMS OF DOPING  
IN PbSe(Se):Bi FILMS

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S u m m a r y

Quasichemical equations describing the formation of point defects in Bi-doped films of plumbum selenide, grown at various deposition temperatures from the vapor phase saturated with selenium, have been proposed. Experimental results are explained by the amphoteric properties of the dopant.